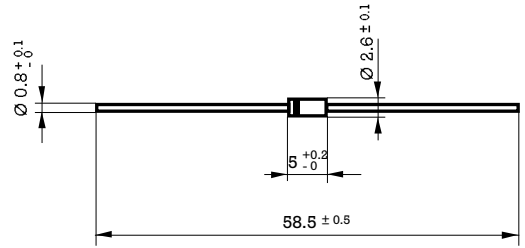


1 Amp. Schottky Barrier Rectifier

<p>Dimensions in mm.</p>  <p>DO-41 (Plastic)</p> <p>Mounting instructions</p> <ol style="list-style-type: none"> 1. Min. distance from body to soldering point, 4 mm. 2. Max. solder temperature, 350 °C. 3. Max. soldering time, 3.5 sec. 4. Do not bend lead at a point closer than 2 mm. to the body. 	<p>Voltage 20 V to 40 V</p> <p>Current 1.0 A at 90 °C.</p>
<ul style="list-style-type: none"> • Metal Silicon Junction, majority carrier conduction • High current capability, low forward voltage drop • Guardring for overvoltage protection • Low power loss, high efficiency • High surge capability • Plastic material carries U/L recognition 94VO • Terminals: Axial Leads • Polarity: Colour band denotes cathode 	

Maximum Ratings, according to IEC publication No. 134

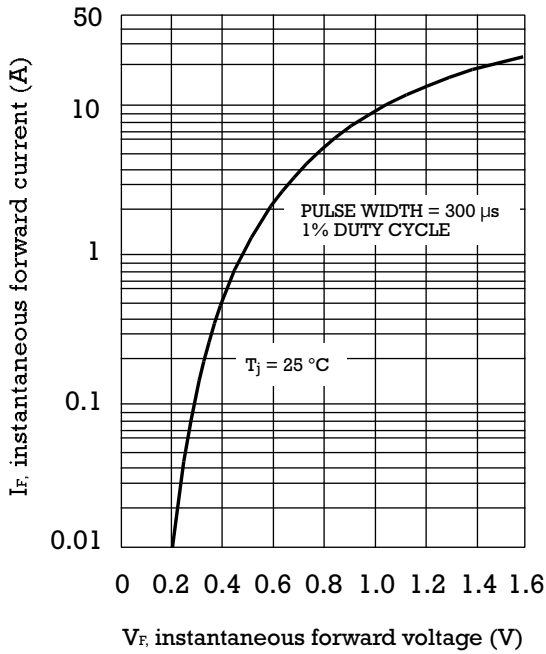
		1N5817	1N5818	1N5819
V_{RRM}	Peak recurrent reverse voltage (V)	20	30	40
V_{RMS}	Maximum RMS voltage (V)	14	21	28
V_{DC}	Maximum DC blocking voltage (V)	20	30	40
V_{RSM}	Maximum non-repetitive peak reverse voltage (V)	24	36	48
$I_{F(AV)}$	Maximum average Forward current. 9.5 mm lead length at $T_L = 90\text{ °C}$	1 A		
I_{FSM}	8.3 ms. peak forward surge current (Jedec Method)	25 A		
C_j	Typical junction capacitance at 1 MHz and $-4V_{DC}$	110 pF		
T_j	Operating temperature range	- 65 to + 125 °C		
T_{stg}	Storage temperature range	- 65 to + 125 °C		

Electrical Characteristics at $T_{amb} = 25\text{ °C}$

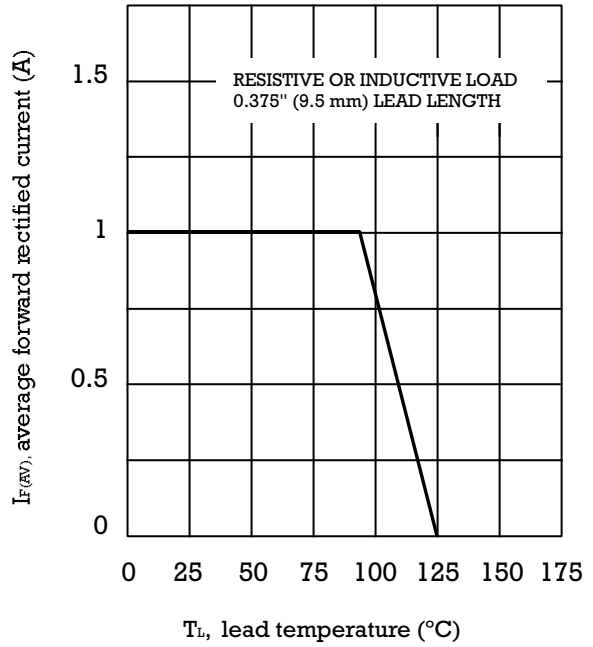
V_F	Max. forward voltage drop at $I_F = 1.0\text{ A}$	0.55 V	0.60 V
I_R	Max. Instantaneous reverse current at V_{RRM}	$T_a = 25\text{ °C}$ 1 mA	$T_a = 100\text{ °C}$ 10 mA
R_{thj-a} R_{thj-l}	Typical Thermal Resistance	50 °C/W 15 °C/W	

NOTE: Thermal Resistance from junction to lead or to ambient PCB mounted with 9.5 mm lead length with 38x38 mm copper pads.

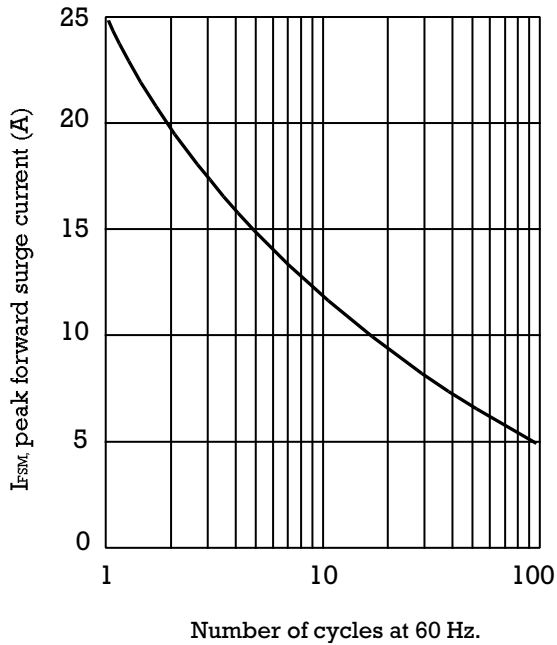
TYPICAL FORWARD CHARACTERISTIC



FORWARD CURRENT DERATING CURVE



MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



TYPICAL JUNCTION CAPACITANCE

